



## STN4NF03L

N-channel 30V - 0.039Ω - 6.5A - SOT-223  
STripFET™ II Power MOSFET

### General features

Type	V <sub>DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub>
STN4NF03L	30V	<0.05Ω	6.5A

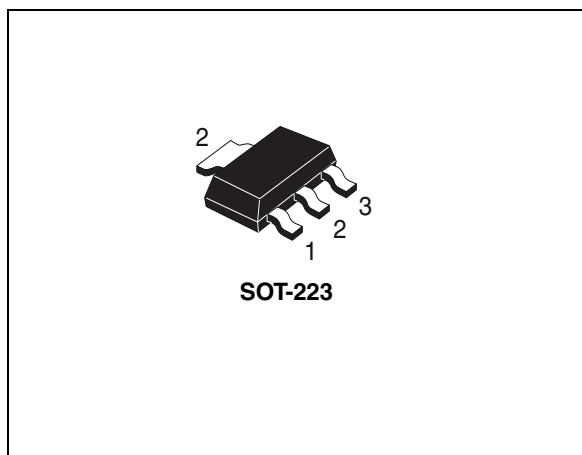
- Low threshold drive

### Description

This Power Mosfet is the latest development of STMicroelectronics unique “Single Feature Size™” strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

### Applications

- Switching application



### Internal schematic diagram



### Order codes

Part number	Marking	Package	Packaging
STN4NF03L	N4NF03L	SOT-223	Tape & reel

# Contents

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# 1 Electrical ratings

**Table 1. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{DS}$	Drain-source voltage ( $V_{GS} = 0$ )	30	V
$V_{GS}$	Gate-source voltage	$\pm 16$	V
$I_D$	Drain current (continuous) at $T_C = 25^\circ\text{C}$	6.5	A
$I_D$	Drain current (continuous) at $T_C = 100^\circ\text{C}$	4.5	A
$I_{DM}^{(1)}$	Drain current (pulsed)	26	A
$P_{TOT}$	Total dissipation at $T_C = 25^\circ\text{C}$	3.3	W
	Derating factor	0.026	W/ $^\circ\text{C}$
$E_{AS}^{(2)}$	Single pulse avalanche energy	200	mJ
$T_J$ $T_{stg}$	Operating junction temperature Storage temperature	-55 to 150	$^\circ\text{C}$

1. Pulse width limited by safe operating area

2. Starting  $T_J = 25^\circ\text{C}$ ,  $I_D = 6.5\text{A}$ ,  $V_{DD} = 15\text{V}$

**Table 2. Thermal data**

Rthj-pcb	Thermal resistance junction-PCB <sup>(1)</sup> max	38	$^\circ\text{C}/\text{W}$
Rthj-pcb	Thermal resistance junction-PCB <sup>(2)</sup> max	100	$^\circ\text{C}/\text{W}$
$T_I$	Maximum lead temperature for soldering purpose (for 10 sec. 1.6 mm from case) typ	260	$^\circ\text{C}$

1. When mounted on 1 in<sup>2</sup> FR-4 board, 2 oz Cu,  $t < 10\text{s}$

2. Minimum recommended footprint

## 2 Electrical characteristics

( $T_{CASE}=25^{\circ}C$  unless otherwise specified)

**Table 3. On/off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 250 \mu A, V_{GS} = 0$	30			V
$I_{DSS}$	Zero gate voltage drain current ( $V_{GS} = 0$ )	$V_{DS} = \text{Max rating},$ $V_{DS} = \text{Max rating} @ 125^{\circ}C$			1 10	$\mu A$ $\mu A$
$I_{GSS}$	Gate body leakage current ( $V_{DS} = 0$ )	$V_{GS} = \pm 16V$			$\pm 100$	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	1			V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10V, I_D = 2A$ $V_{GS} = 5V, I_D = 2A$		0.039 0.046	0.05 0.06	$\Omega$ $\Omega$

**Table 4. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$g_{fs}^{(1)}$	Forward transconductance	$V_{DS}=10V, I_D=1A$	3	6		S
$C_{iss}$ $C_{oss}$ $C_{rss}$	Input capacitance Output capacitance Reverse transfer capacitance	$V_{DS}=25V, f=1 \text{ MHz}, V_{GS}=0$		330 90 40		pF pF pF
$Q_g$ $Q_{gs}$ $Q_{gd}$	Total gate charge Gate-source charge Gate-drain charge	$V_{DD}=24V, I_D = 4A$ $V_{GS} = 10V$ (see Figure 13)		6.5 3.2 2	9	nC nC nC

1. Pulsed: pulse duration=300 $\mu s$ , duty cycle 1.5%

**Table 5. Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ $t_r$	Turn-on delay time rise time	$V_{DD}=15 V, I_D=2A,$ $R_G=4.7\Omega, V_{GS}=4.5V$ (see Figure 14)		11 100		ns ns
$t_{d(off)}$ $t_f$	Turn-off-delay time fall time	$V_{DD}=15 V, I_D=2A,$ $R_G=4.7\Omega, V_{GS}=4.5V$ (see Figure 14)		35 22		ns ns

**Table 6. Source drain diode**

Symbol	Parameter	Test conditions	Min	Typ.	Max	Unit
$I_{SD}$	Source-drain current				6.5	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)				26	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD}=6.5A, V_{GS}=0$			1.5	V
$t_{rr}$	Reverse recovery time	$I_{SD}=6.5 A,$ $di/dt = 100A/\mu s,$ $V_{DD}=15 V, T_j=150^\circ C$ (see Figure 14)		34		ns
$Q_{rr}$	Reverse recovery charge			25		nC
$I_{RRM}$	Reverse recovery current			1.4		A

1. Pulse width limited by safe operating area.
2. Pulsed: pulse duration=300 $\mu s$ , duty cycle 1.5%

## 2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

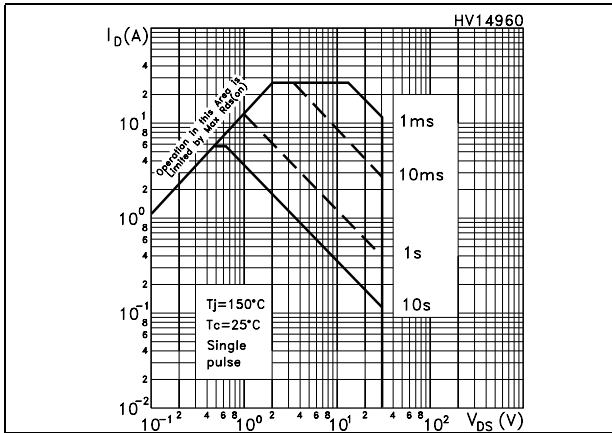


Figure 2. Thermal impedance junction-PCB

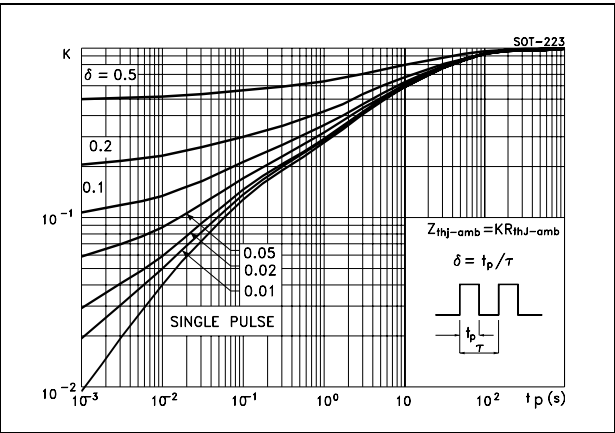


Figure 3. Output characteristics

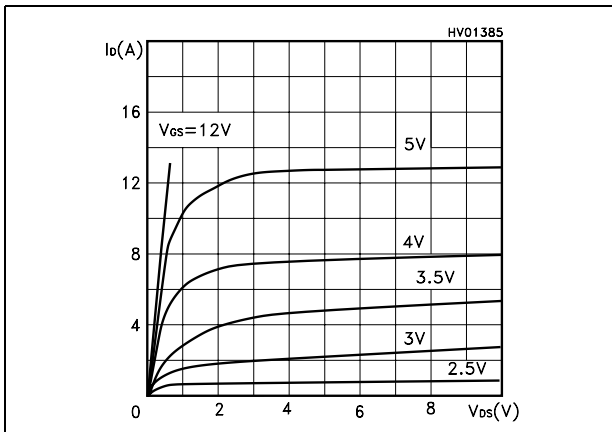


Figure 4. Transfer characteristics

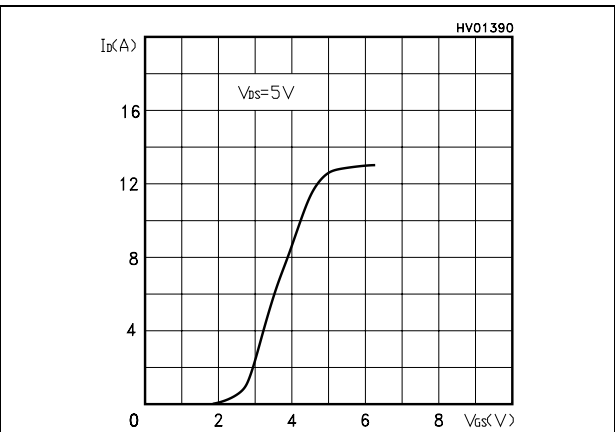


Figure 5. Transconductance

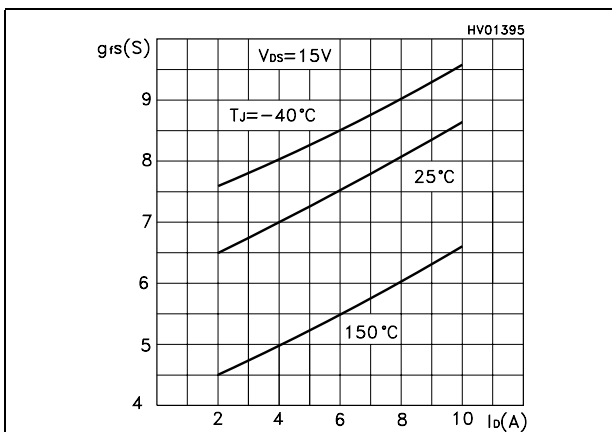


Figure 6. Static drain-source on resistance

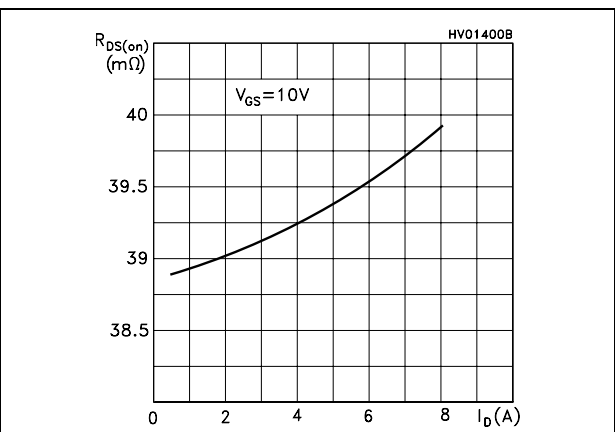


Figure 7. Gate charge vs gate-source voltage Figure 8. Capacitance variations

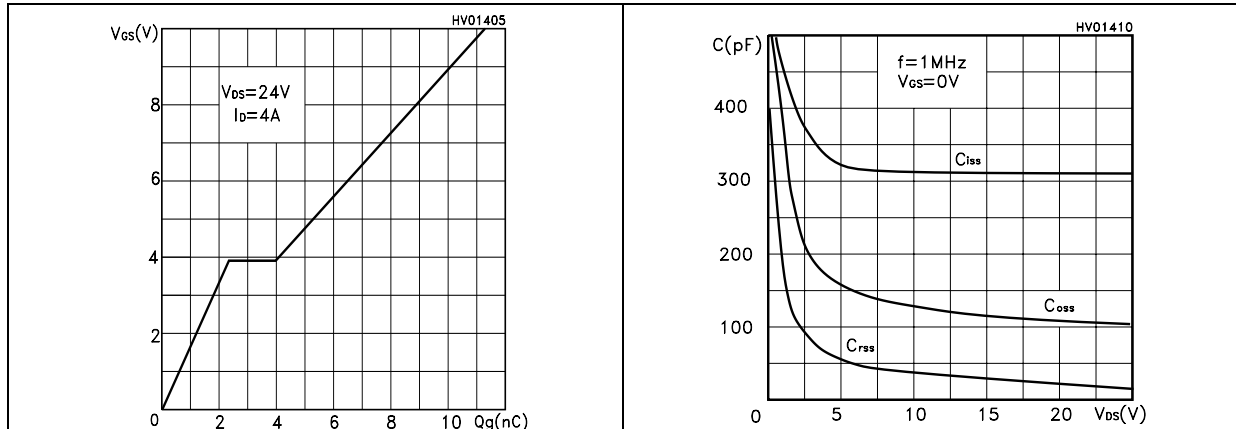


Figure 9. Normalized gate threshold voltage vs temperature Figure 10. Normalized on resistance vs temperature

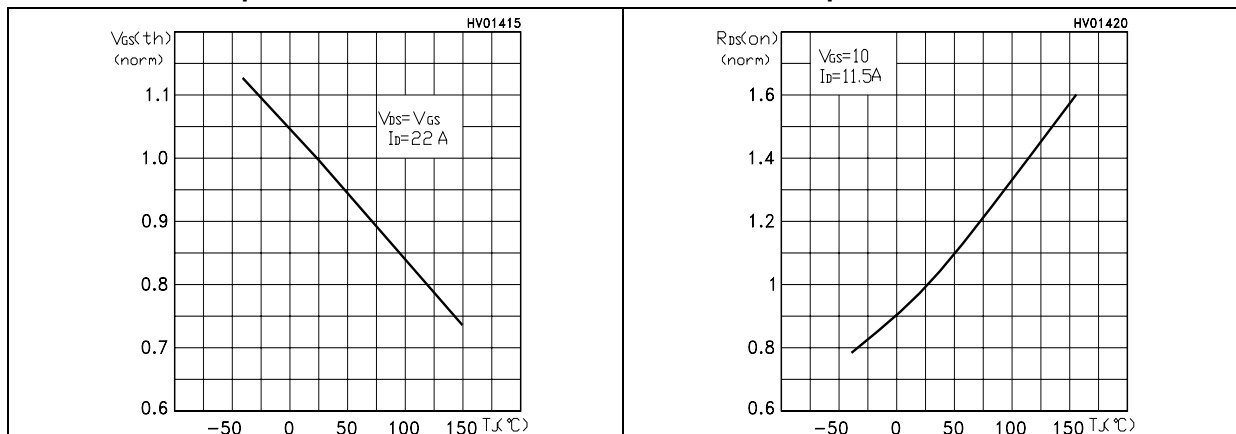
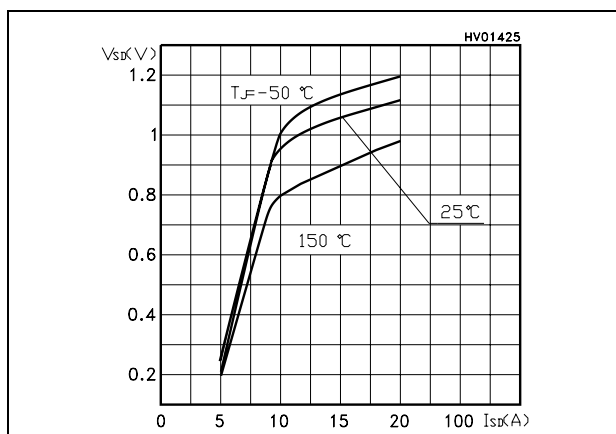


Figure 11. Source-drain diode forward characteristics



### 3 Test circuit

Figure 12. Switching times test circuit for resistive load

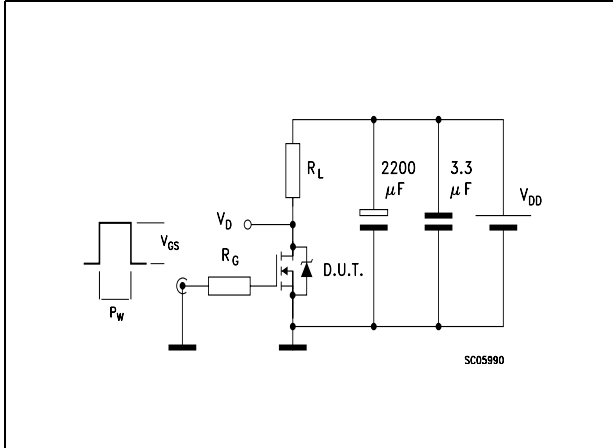


Figure 13. Gate charge test circuit

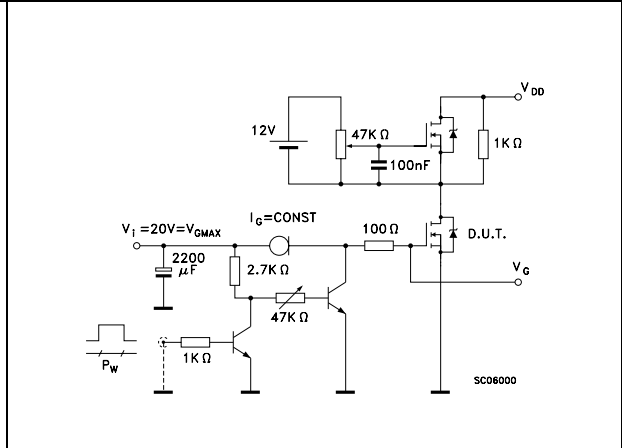


Figure 14. Test circuit for inductive load switching and diode recovery times



Figure 15. Unclamped Inductive load test circuit

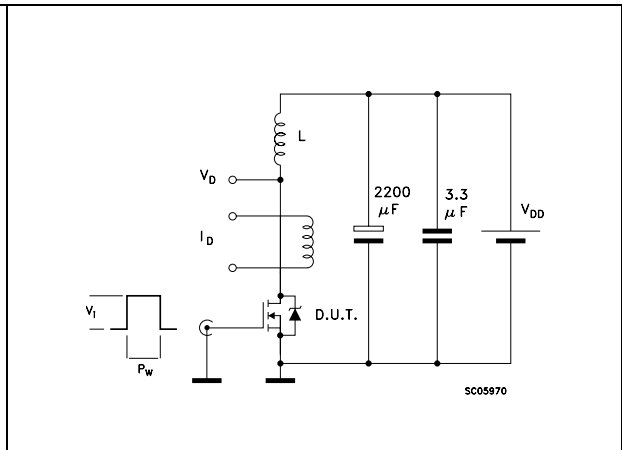


Figure 16. Unclamped inductive waveform

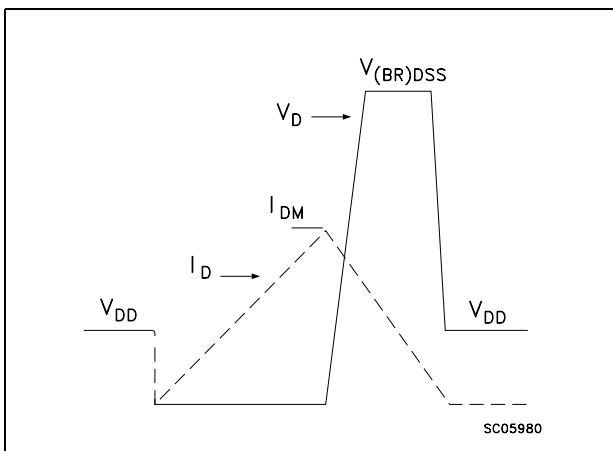
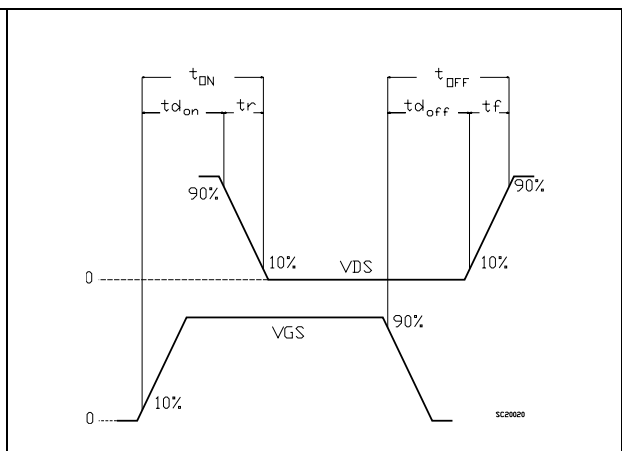


Figure 17. Switching time waveform



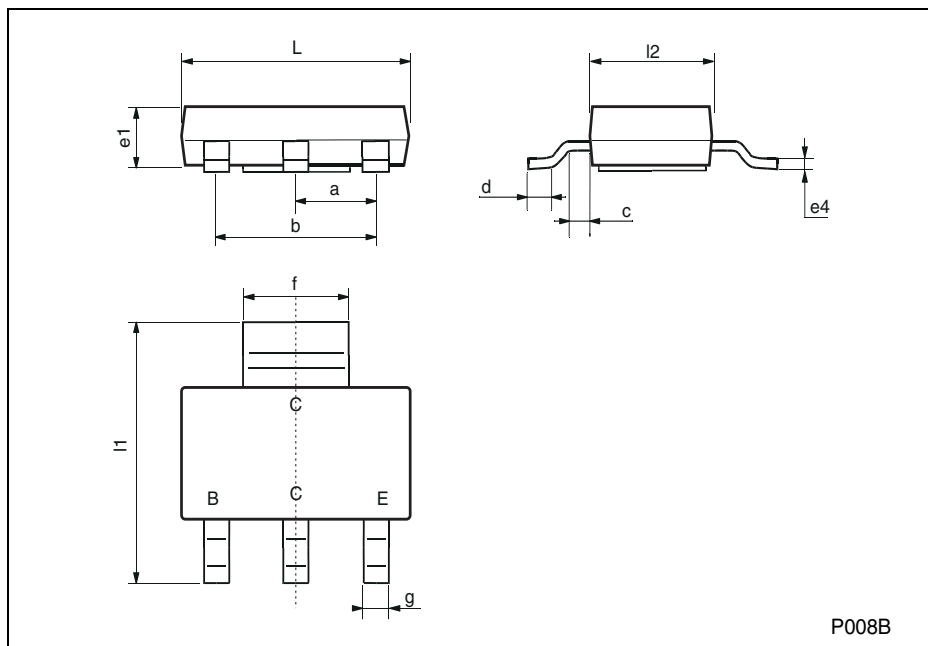


## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: [www.st.com](http://www.st.com)

**SOT-223 MECHANICAL DATA**

DIM.	mm			mils		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a	2.27	2.3	2.33	89.4	90.6	91.7
b	4.57	4.6	4.63	179.9	181.1	182.3
c	0.2	0.4	0.6	7.9	15.7	23.6
d	0.63	0.65	0.67	24.8	25.6	26.4
e1	1.5	1.6	1.7	59.1	63	66.9
e4			0.32			12.6
f	2.9	3	3.1	114.2	118.1	122.1
g	0.67	0.7	0.73	26.4	27.6	28.7
l1	6.7	7	7.3	263.8	275.6	287.4
l2	3.5	3.5	3.7	137.8	137.8	145.7
L	6.3	6.5	6.7	248	255.9	263.8



## 5 Revision history

**Table 7. Revision history**

<b>Date</b>	<b>Revision</b>	<b>Changes</b>
21-Jun-2004	3	Complete document
09-Oct-2006	4	New template, no content change

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